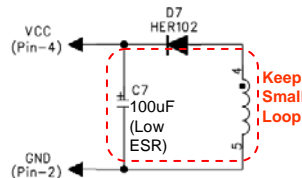


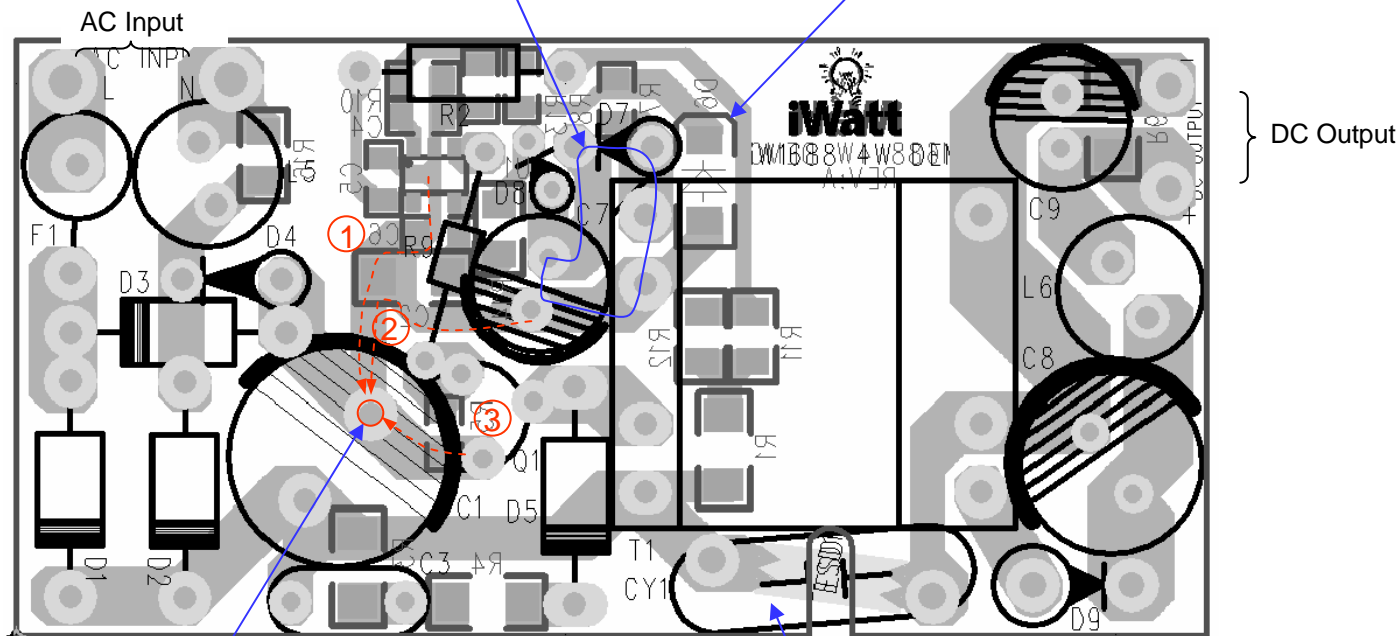
Recommended PCB Layout for iW1688

辅助线圈回路：
在 D7 & C7 之间
保持最短距离

Bias Supply Loop :
Keep shortest
distance between D7
& C7



Vsense reset Diode (D6) : Vsense 复位二级
管 (D7) :
Allow direct connection
between D6's Anode
(1N4148) to Bias winding's
return. D6(1N4148)阳极
直接连接到偏置
绕组的地端



Common Ground Node :
Make Individual connection path to this
Grounding Node.

- ① 1688's pin-2,
- ② Bias winding return &
- ③ Power FET's Source

共地点：
单独连接地线路到大地点

- ① 1688's 2 脚,
- ② 偏置绕组回路地
- ③ 功率(FET)

Y-cap:
When Y-cap is used, connect
between B(+) and Secondary
GND for Good PLT and ESD
immunity.

Y-电容：
使用 Y-电容,B(+)
和次级地之间连
接以得到好的
PLT和ESD耐受。

Components Selection Guide for iW1688

Act as fuse and current limiting.
Used wire-wound type for best PL Surge withstanding

作为保险丝和电流限制，用线绕级来达到最好PL浪涌裕量

Individual Diodes
best for lowest cost
单独的二极管是为了更低的成本

Vin Resistors
Minimum 2 in series for best HV reliability. (Preferred 1%)

Vin 电阻最小2个串联级到最好的HV可靠性。(首选1%)

Preferred UF Diode
首选UF 二极管

Radial/Axial type with 0.3A current rating (preferred Dia=8mm).
0.3A电流级别的线状/轴向式(首选Dia=8mm)

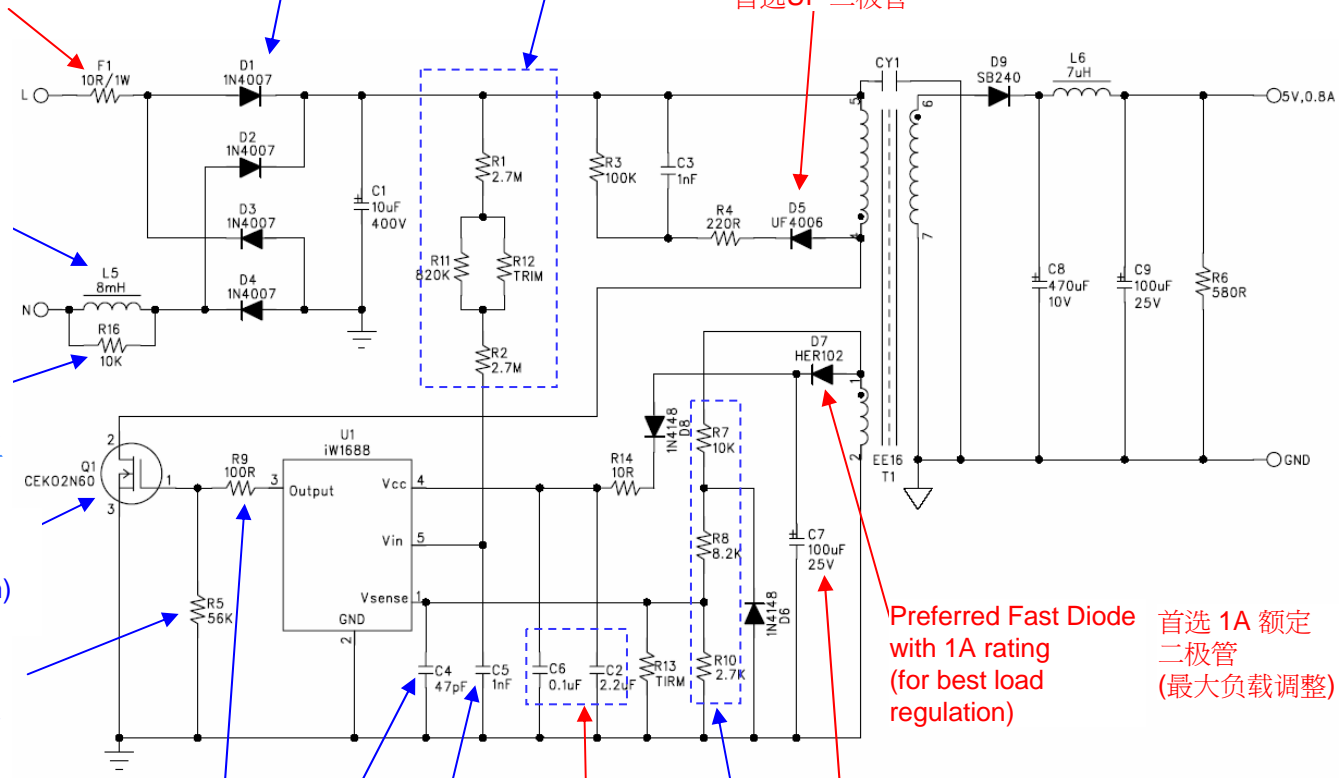
De-resonance resistor.
防止谐振的电阻

额定值: 例如. 600V/1A (15ohm)在4W设计里

General Rating: e.g. 600V/1A (15ohm) for a 4W design

MOSFET gate Discharge resistor (do not eliminate)

MOSFET 放电电阻 (不能删除)



Gate charge control for EMI
门级电荷控制 EMI

Vsense filtering
Vsense 滤波电容

Vin filtering
Vin 滤波电容

Vcc filtering (SMD with X7R type)
Vcc滤波电容 (X7R贴片)

Low ESR 低ESR - 电
E-cap 解电容

For Vout setting. Vout 设计电阻 (Preferred 1%) (首选 1%)

Preferred Fast Diode with 1A rating (for best load regulation)

首选 1A 额定二极管 (最大负载调整)

■ 一般建议
■ 推荐使用的关键元件